
HM62W8512A Series

524288-word \times 8-bit High Speed CMOS Static RAM

HITACHI

ADE-203-641 (Z)
Preliminary
Rev. 0.0
Oct. 3, 1996

Description

The Hitachi HM62W8512A is a 4-Mbit static RAM organized 512-kword \times 8-bit. It realizes higher density, higher performance and low power consumption by employing 0.5 μ m Hi-CMOS process technology. The device, packaged in a 525-mil SOP (foot print pitch width) or 400-mil TSOP TYPE II is available for high density mounting. The HM62W8512A is suitable for battery backup system.

Features

- Single 3.3 V supply
- Access time: 70/85 ns (max)
- Power dissipation
 - Active: 36 mW/MHz (max)
 - Standby: 4 μ W (typ)
- Completely static memory. No clock or timing strobe required
- Equal access and cycle times
- Common data input and output: Three state output
- Directly LV-TTL compatible: All inputs and outputs
- Battery backup operation

Preliminary: This document contains information on a new product. Specifications and information contained herein are subject to change without notice.

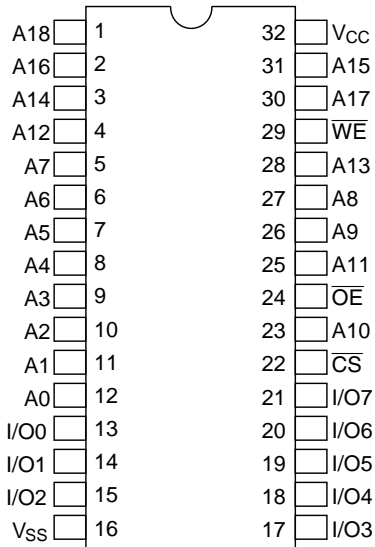
HM62W8512A Series

Ordering Information

Type No.	Access time	Package
HM62W8512ALFP-7	70 ns	525-mil 32-pin plastic SOP (FP-32D)
HM62W8512ALFP-8	85 ns	
HM62W8512ALFP-7SL	70 ns	
HM62W8512ALFP-8SL	85 ns	
HM62W8512ALTT-7	70 ns	400-mil 32-pin plastic TSOP II (TTP-32D)
HM62W8512ALTT-8	85 ns	
HM62W8512ALTT-7SL	70 ns	
HM62W8512ALTT-8SL	85 ns	
HM62W8512ALRR-7	70 ns	400-mil 32-pin plastic TSOP II reverse (TTP-32DR)
HM62W8512ALRR-8	85 ns	
HM62W8512ALRR-7SL	70 ns	
HM62W8512ALRR-8SL	85 ns	

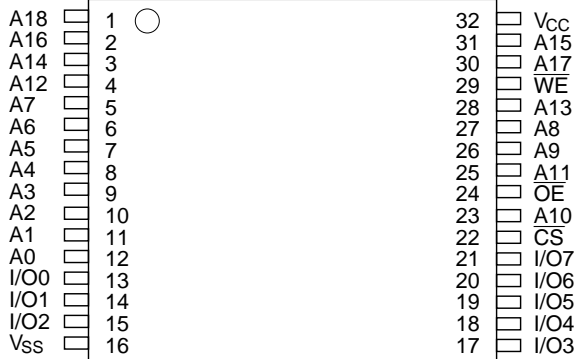
Pin Arrangement

HM62W8512ALFP Series



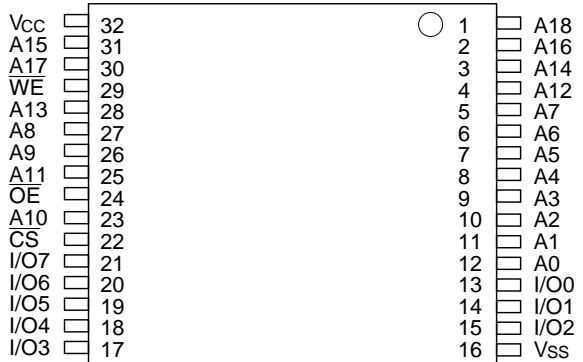
(Top view)

HM62W8512ALTT Series



(Top view)

HM62W8512ALRR Series

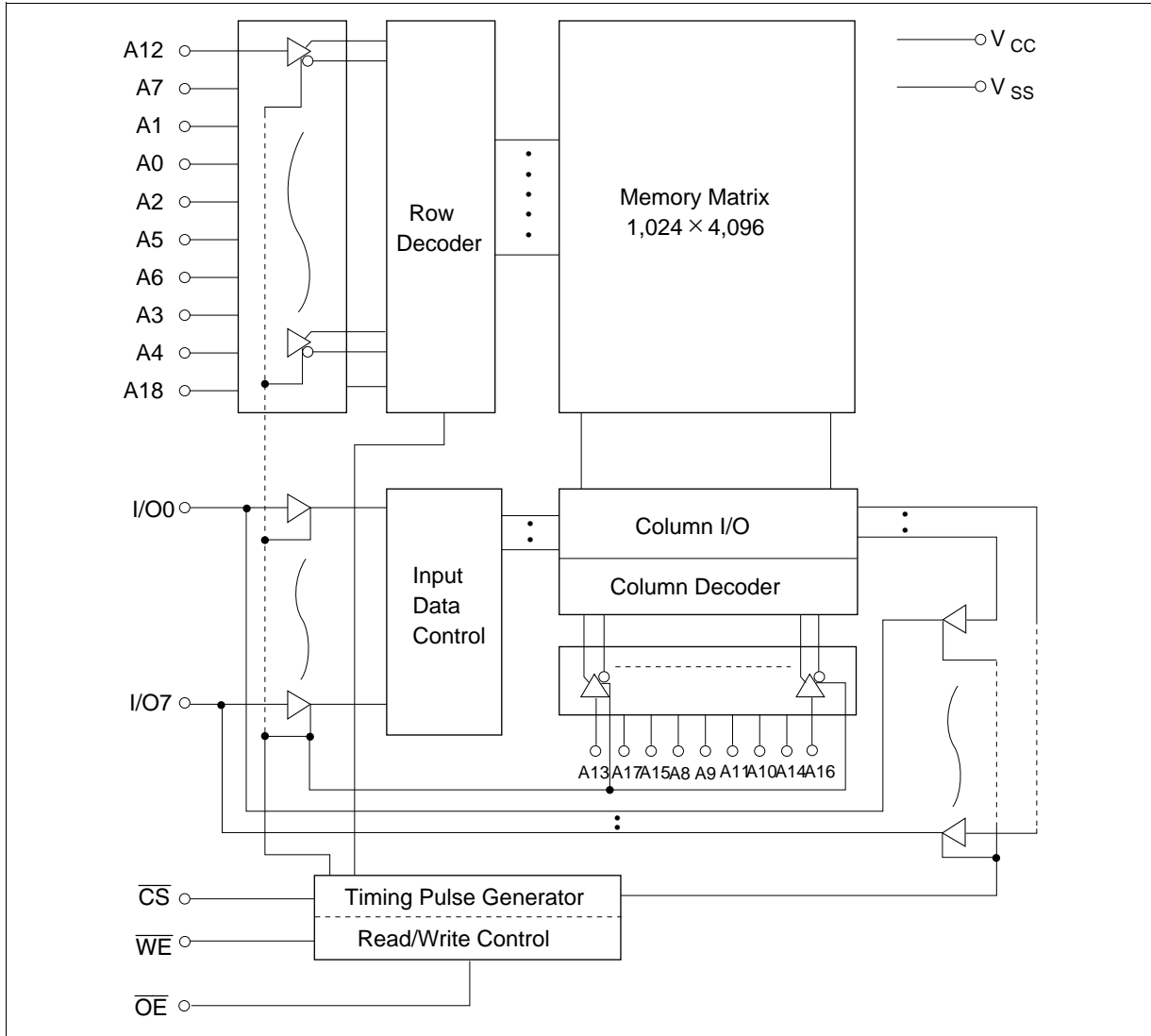


(Top view)

Pin Description

Pin name	Function
A0 to A18	Address input
I/O0 to I/O7	Data input/output
CS	Chip select
OE	Output enable
WE	Write enable
V _{CC}	Power supply
V _{SS}	Ground

Block Diagram



Function Table

\overline{WE}	\overline{CS}	\overline{OE}	Mode	V_{CC} current	Dout pin	Ref. cycle
×	H	×	Not selected	I_{SB}, I_{SB1}	High-Z	—
H	L	H	Output disable	I_{CC}	High-Z	—
H	L	L	Read	I_{CC}	Dout	Read cycle
L	L	H	Write	I_{CC}	Din	Write cycle (1)
L	L	L	Write	I_{CC}	Din	Write cycle (2)

Note: ×: H or L

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Power supply voltage	V_{CC}	-0.5 to +4.6	V
Voltage on any pin relative to V_{SS}	V_T	-0.5* ¹ to $V_{CC} + 0.5$ * ²	V
Power dissipation	P_T	1.0	W
Operating temperature	T_{opr}	0 to +70	°C
Storage temperature	T_{stg}	-55 to +125	°C
Storage temperature under bias	T_{bias}	-10 to +85	°C

Notes: 1. -3.0 V for pulse half-width ≤ 30 ns
 2. Maximum voltage is 4.6 V

Recommended DC Operating Conditions (Ta = 0 to +70°C)

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage	V_{CC}	3.0	3.3	3.6	V
	V_{SS}	0	0	0	V
Input high voltage	V_{IH}	2.0	—	$V_{CC} + 0.3$	V
Input low voltage	V_{IL}	-0.3* ¹	—	0.8	V

Note: 1. -3.0 V for pulse half-width ≤ 30 ns

HM62W8512A Series

DC Characteristics (Ta = 0 to +70°C, V_{CC} = 3.3 V ±0.3 V, V_{SS} = 0 V)

Parameter	Symbol	Min	Typ* ¹	Max	Unit	Test conditions	
Input leakage current	I _{LI}	—	—	1	μA	V _{in} = V _{SS} to V _{CC}	
Output leakage current	I _{LO}	—	—	1	μA	$\overline{CS} = V_{IH}$ or $\overline{OE} = V_{IH}$ or $\overline{WE} = V_{IL}$, V _{I/O} = V _{SS} to V _{CC}	
Operating power supply current: DC	I _{CC}	—	—	10	mA	$\overline{CS} = V_{IL}$, others = V _{IH} /V _{IL} , I _{I/O} = 0 mA	
Operating power supply current	HM62W8512A-7	I _{CC1}	—	—	30	mA	Min cycle, duty = 100% $\overline{CS} = V_{IL}$, others = V _{IH} /V _{IL} I _{I/O} = 0 mA
	HM62W8512A-8	I _{CC1}	—	—	27	mA	
Operating power supply current	I _{CC2}	—	—	10	mA	Cycle time = 1 μs, duty = 100% I _{I/O} = 0 mA, $\overline{CS} \leq 0.2$ V V _{IH} ≥ V _{CC} - 0.2 V, V _{IL} ≤ 0.2 V	
Standby power supply current: DC	I _{SB}	—	0.1	0.3	mA	$\overline{CS} = V_{IH}$	
Standby power supply current (1): DC	I _{SB1}	—	1.2* ²	70* ²	μA	V _{in} ≥ 0 V, $\overline{CS} \geq V_{CC} - 0.2$ V	
			—	1.2* ³	30* ³	μA	
Output low voltage	V _{OL}	—	—	0.4	V	I _{OL} = 2.0 mA	
				0.2	V	I _{OL} = 100 μA	
Output high voltage	V _{OH}	V _{CC} - 0.2	—	—	V	I _{OH} = -100 μA	
				2.4	V	I _{OH} = -2.0 mA	

- Notes: 1. Typical values are at V_{CC} = 3.3 V, Ta = +25°C and specified loading, and not guaranteed.
 2. This characteristics is guaranteed only for L version.
 3. This characteristics is guaranteed only for L-SL version.

Capacitance (Ta = 25°C, f = 1 MHz)

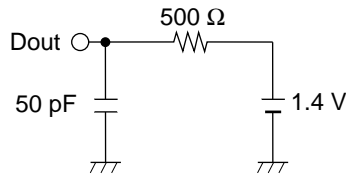
Parameter	Symbol	Typ	Max	Unit	Test conditions
Input capacitance* ¹	C _{in}	—	8	pF	V _{in} = 0 V
Input/output capacitance* ¹	C _{I/O}	—	10	pF	V _{I/O} = 0 V

- Note: 1. This parameter is sampled and not 100% tested.

AC Characteristics ($T_a = 0$ to $+70^\circ\text{C}$, $V_{CC} = 3.3\text{ V} \pm 0.3\text{ V}$, unless otherwise noted.)

Test Conditions

- Input pulse levels: 0.4 V to 2.4 V
- Input rise and fall time: 5 ns
- Input timing reference levels: 1.4 V
- Output timing reference level: 0.8 V/2.0 V
- Output load (Including scope & jig)



Read Cycle

Parameter	Symbol	HM62W8512A				Unit	Notes
		-7		-8			
		Min	Max	Min	Max		
Read cycle time	t_{RC}	70	—	85	—	ns	
Address access time	t_{AA}	—	70	—	85	ns	
Chip select access time	t_{CO}	—	70	—	85	ns	
Output enable to output valid	t_{OE}	—	35	—	45	ns	
Chip selection to output in low-Z	t_{LZ}	10	—	10	—	ns	2
Output enable to output in low-Z	t_{OLZ}	5	—	5	—	ns	2
Chip deselection to output in high-Z	t_{HZ}	0	30	0	35	ns	1, 2
Output disable to output in high-Z	t_{OHZ}	0	30	0	35	ns	1, 2
Output hold from address change	t_{OH}	10	—	10	—	ns	

HM62W8512A Series

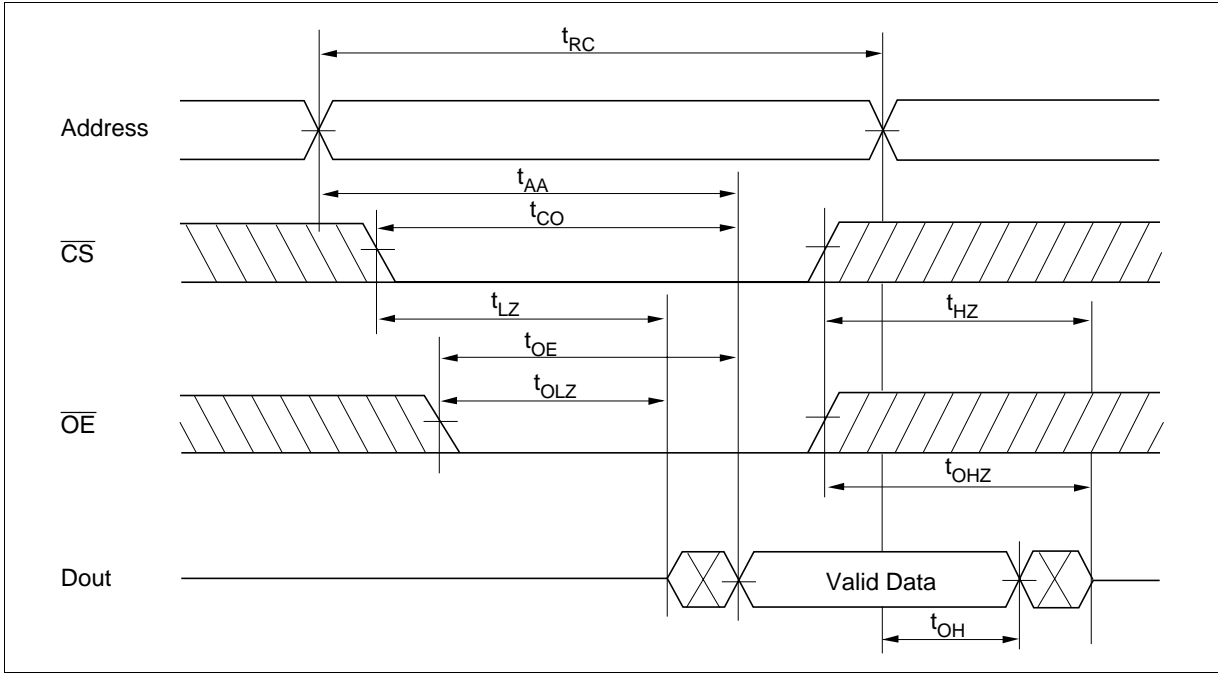
Write Cycle

Parameter	Symbol	HM62W8512A				Unit	Notes
		-7		-8			
		Min	Max	Min	Max		
Write cycle time	t_{WC}	70	—	85	—	ns	
Chip selection to end of write	t_{CW}	60	—	75	—	ns	4
Address setup time	t_{AS}	0	—	0	—	ns	5
Address valid to end of write	t_{AW}	60	—	75	—	ns	
Write pulse width	t_{WP}	50	—	55	—	ns	3, 12
Write recovery time	t_{WR}	0	—	0	—	ns	6
\overline{WE} to output in high-Z	t_{WHZ}	0	30	0	35	ns	1, 2, 7
Data to write time overlap	t_{DW}	30	—	35	—	ns	
Data hold from write time	t_{DH}	0	—	0	—	ns	
Output active from output in high-Z	t_{OW}	5	—	5	—	ns	2
Output disable to output in high-Z	t_{OHZ}	0	30	0	35	ns	1, 2, 7

- Notes:
1. t_{HZ} , t_{OHZ} and t_{WHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.
 2. This parameter is sampled and not 100% tested.
 3. A write occurs during the overlap (t_{WP}) of a low \overline{CS} and a low \overline{WE} . A write begins at the later transition of \overline{CS} going low or \overline{WE} going low. A write ends at the earlier transition of \overline{CS} going high or \overline{WE} going high. t_{WP} is measured from the beginning of write to the end of write.
 4. t_{CW} is measured from \overline{CS} going low to the end of write.
 5. t_{AS} is measured from the address valid to the beginning of write.
 6. t_{WR} is measured from the earlier of \overline{WE} or \overline{CS} going high to the end of write cycle.
 7. During this period, I/O pins are in the output state so that the input signals of the opposite phase to the outputs must not be applied.
 8. If the \overline{CS} low transition occurs simultaneously with the \overline{WE} low transition or after the \overline{WE} transition, the output remain in a high impedance state.
 9. $Dout$ is the same phase of the write data of this write cycle.
 10. $Dout$ is the read data of next address.
 11. If \overline{CS} is low during this period, I/O pins are in the output state. Therefore, the input signals of the opposite phase to the outputs must not be applied to them.
 12. In the write cycle with \overline{OE} low fixed, t_{WP} must satisfy the following equation to avoid a problem of data bus contention. $t_{WP} \geq t_{DW} \text{ min} + t_{WHZ} \text{ max}$

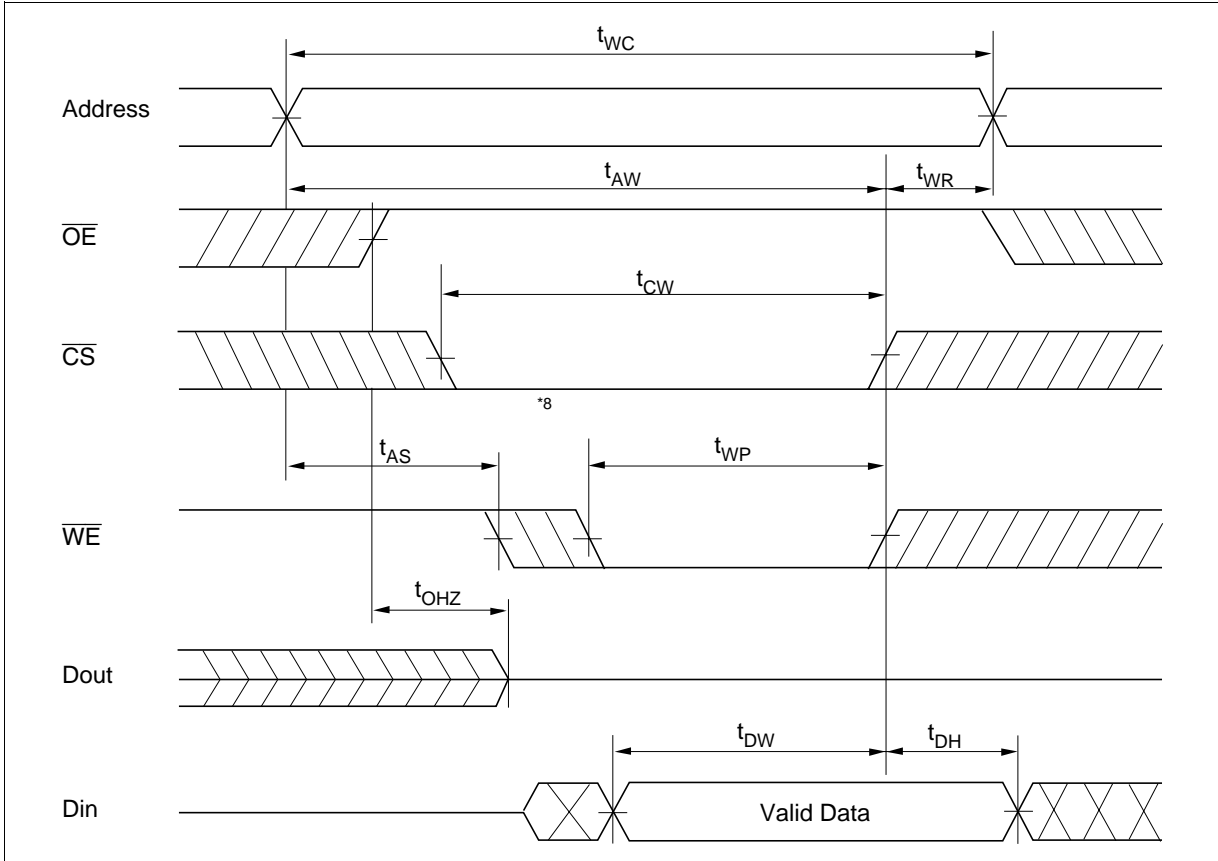
Timing Waveforms

Read Timing Waveform ($\overline{WE} = V_{IH}$)

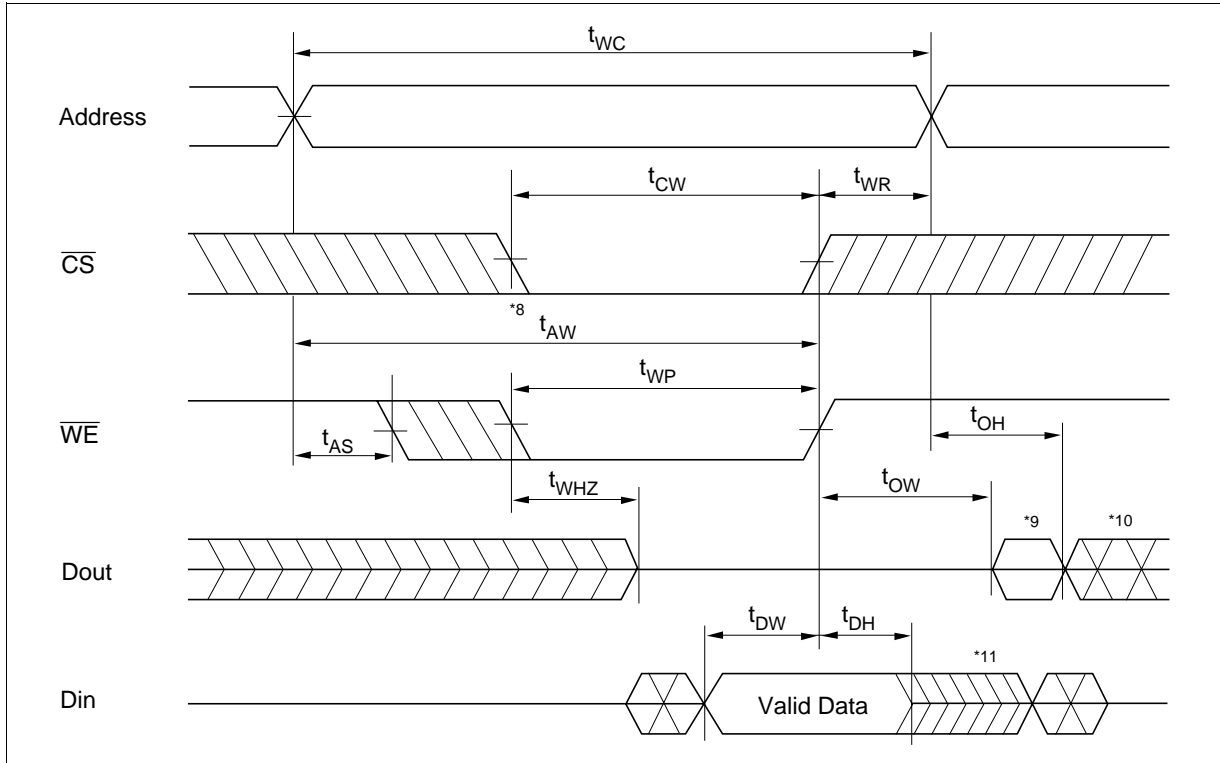


HM62W8512A Series

Write Timing Waveform (1) (\overline{OE} Clock)



Write Timing Waveform (2) ($\overline{\text{OE}}$ Low Fixed)



Low V_{CC} Data Retention Characteristics ($T_a = 0$ to $+70^\circ\text{C}$)

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions*3
V_{CC} for data retention	V_{DR}	2	—	—	V	$\overline{CS} \geq V_{CC} - 0.2\text{ V}$, $V_{in} \geq 0\text{ V}$
Data retention current	I_{CCDR}	—	1^{*4}	50^{*1}	μA	$V_{CC} = 3.0\text{ V}$, $V_{in} \geq 0\text{ V}$ $\overline{CS} \geq V_{CC} - 0.2\text{ V}$
		—	1^{*4}	15^{*2}	μA	
Chip deselect to data retention time	t_{CDR}	0	—	—	ns	See retention waveform
Operation recovery time	t_R	5	—	—	ms	

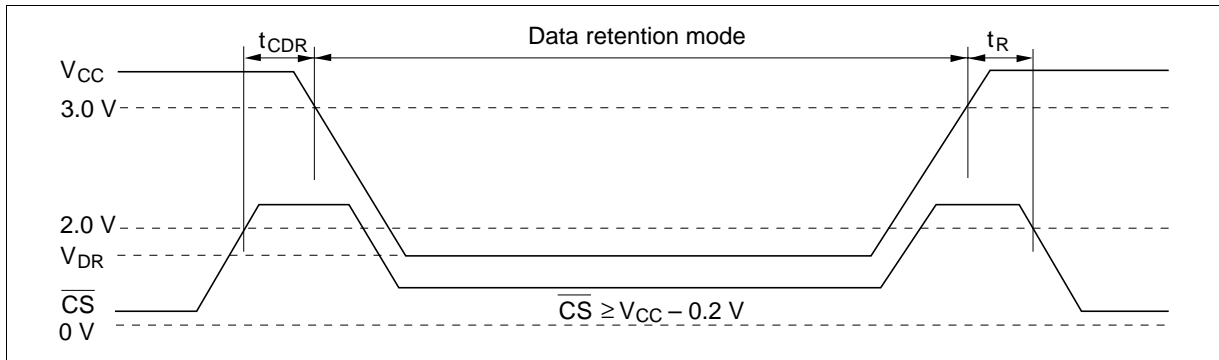
Notes: 1. For L-version and $20\ \mu\text{A}$ (max.) at $T_a = 0$ to 40°C .

2. For SL-version and $3\ \mu\text{A}$ (max.) at $T_a = 0$ to 40°C .

3. \overline{CS} controls address buffer, \overline{WE} buffer, \overline{OE} buffer, and D_{in} buffer. In data retention mode, V_{in} levels (address, \overline{WE} , \overline{OE} , I/O) can be in the high impedance state.

4. Typical values are at $V_{CC} = 3.0\text{ V}$, $T_a = 25^\circ\text{C}$ and specified loading, and not guaranteed.

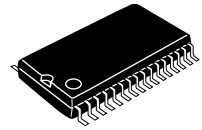
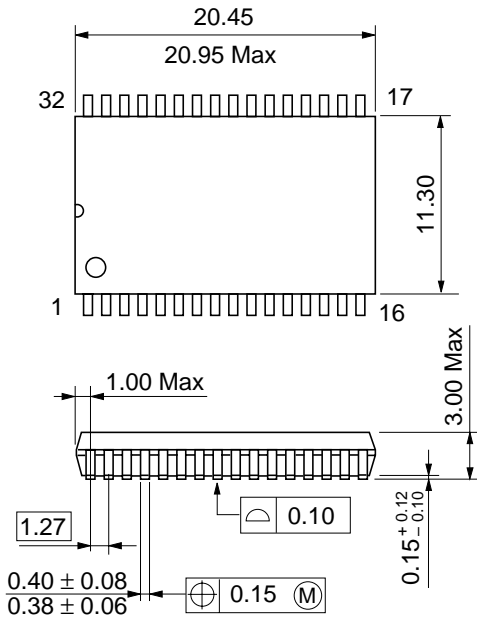
Low V_{CC} Data Retention Timing Waveform (\overline{CS} Controlled)



Package Dimensions

HM62W8512ALFP Series (FP-32D)

Unit: mm

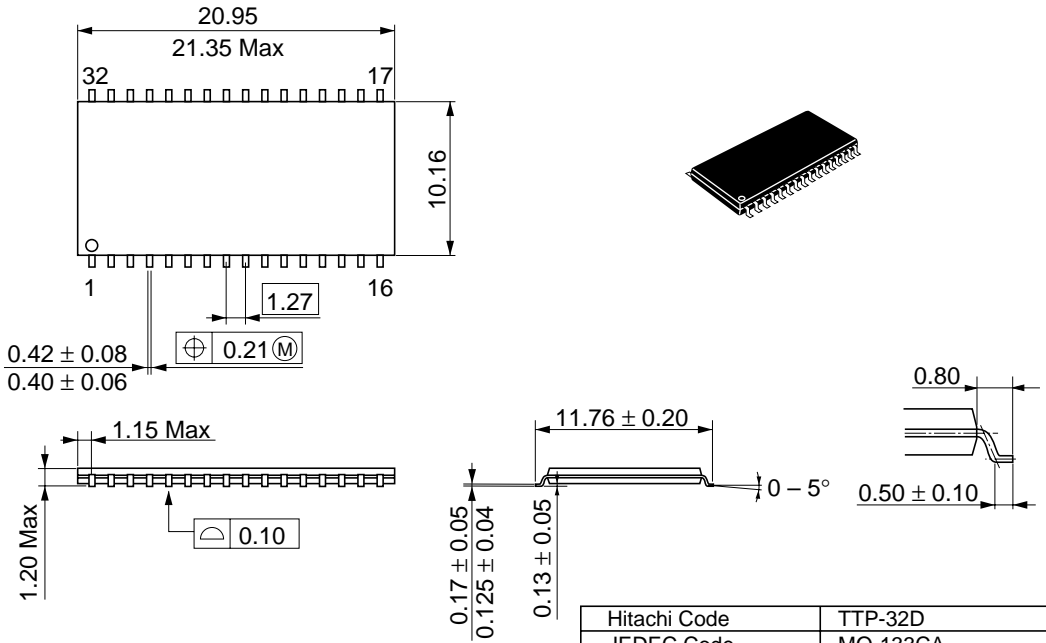


Hitachi Code	FP-32D
JEDEC Code	—
EIAJ Code	—
Weight	1.3 g

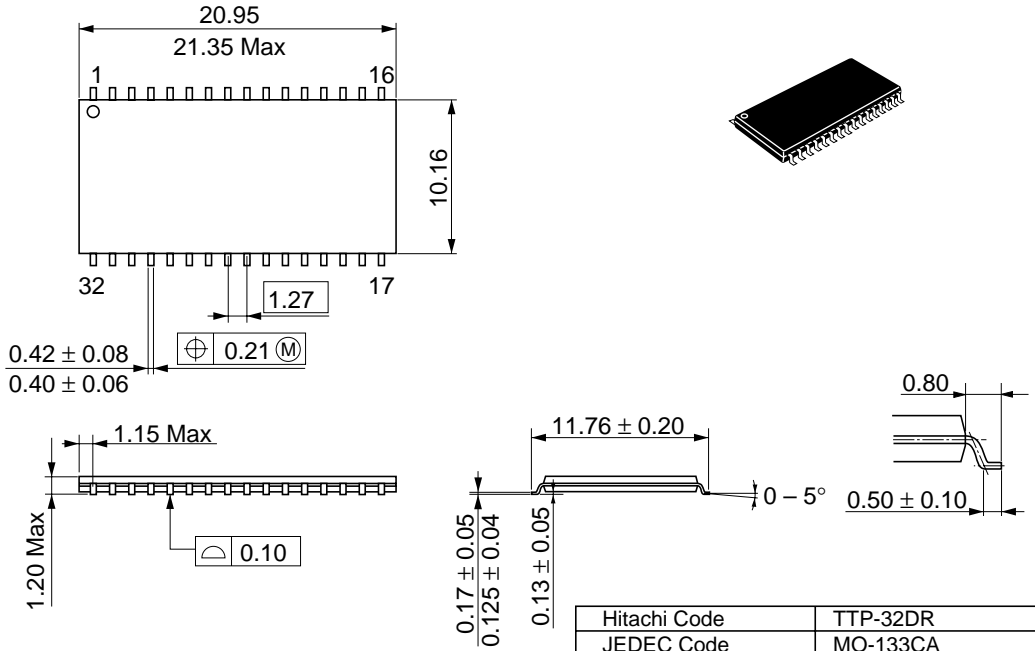
HM62W8512A Series

HM62W8512ALTT Series (TTP-32D)

Unit: mm



Hitachi Code	TTP-32D
JEDEC Code	MO-133CA
EIAJ Code	—
Weight	0.51 g



Hitachi Code	TTP-32DR
JEDEC Code	MO-133CA
EIAJ Code	—
Weight	0.51 g

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0.0	Oct. 3, 1996	Initial issue		
